

## <TRANSISTOR ARRAY>

# M54562FP

**8-UNIT 500mA DARLINGTON TRANSISTOR ARRAY WITH CLAMP DIODE  
SOURCE TYPE**

### DESCRIPTION

M54562FP is an eight-circuit output-sourcing darlington transistor array. The circuits are made of PNP and NPN transistors. This semiconductor integrated circuit performs high current driving with extremely low input-current supply.

### FEATURES

- High breakdown voltage ( $BV_{CEO} \geq 50V$ )
- High-current driving ( $I_o(max) = -500mA$ )
- With clamping diodes
- Driving available with PMOS IC output of 6 ~ 16V or with TTL output
- Output current-sourcing type

### APPLICATIONS

Drives of relays, printers, LEDs, fluorescent display tubes and lamps, and interfaces between MOS-bipolar logic systems and relays, solenoids, or small motors.

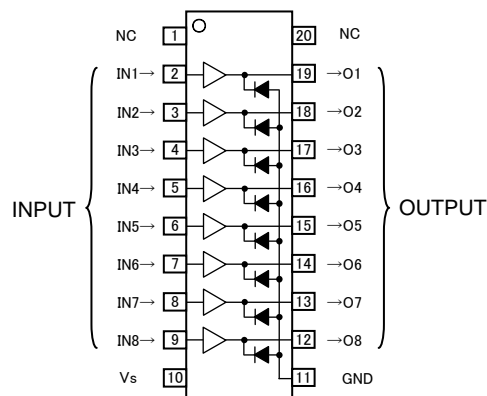
### FUNCTION

The M54562FP each have eight circuits, which are made of input inverters and current-sourcing outputs.

The outputs are made of PNP transistors and NPN Darlington transistors. The PNP transistor base current is constant. A clamping diode is provided between each output and GND. VS and GND are used commonly among the eight circuits.

The inputs have resistance of 8.5k $\Omega$ , and voltage of up to 30V is applicable. Output current is 500 mA maximum. Supply voltage VS is 50V maximum.

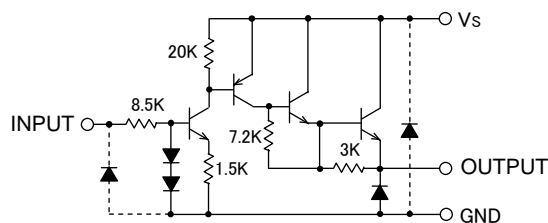
### PIN CONFIGURATION



Package type 20P2N-A

NC : No connection

### CIRCUIT DIAGRAM



The eight circuits share the VS and GND.

The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit : $\Omega$

### ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted, $T_a = -20 \sim +75^\circ C$ )

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CEO}$ #	Collector-emitter voltage	Output , L	-0.5 ~ +50	V
$V_s$	Supply voltage		50	V
$V_i$	Input voltage		-0.5 ~ +30	V
$I_o$	Output current	Current per circuit output, H	- 500	mA
$I_F$	Clamping diode forward current		- 500	mA
$V_R$ #	Clamping diode reverse voltage		50	V
$P_d$	Power dissipation	$T_a = 25^\circ C$ , when mounted on board	1.10	W
$T_{opr}$	Operating temperature		-20 ~ +75	$^\circ C$
$T_{stg}$	Storage temperature		-55 ~ +125	$^\circ C$

# : Unused Input pins must be connected to GND.

## &lt;TRANSISTOR ARRAY&gt;

**M54562FP****8-UNIT 500mA DARLINGTON TRANSISTOR ARRAY WITH CLAMP DIODE  
SOURCE TYPE****RECOMMENDED OPERATING** (Unless otherwise noted,  $T_a = -20 \sim +75^\circ\text{C}$ )

Symbol	Parameter		Limits			Unit
			min	typ	max	
Vs	Supply voltage		0	—	50	V
Io	Output current (Current per 1 circuit when 8 circuits are coming on simultaneously)	Duty Cycle no more than 5%	0	—	−350	mA
		Duty Cycle no more than 30%	0	—	−100	
VIH	“H” input voltage		2.4	5.0	30	V
VIL	“L” input voltage		0	—	0.2	V

**ELECTRICAL CHARACTERISTICS** (Unless otherwise noted,  $T_a = -20 \sim +75^\circ\text{C}$ )

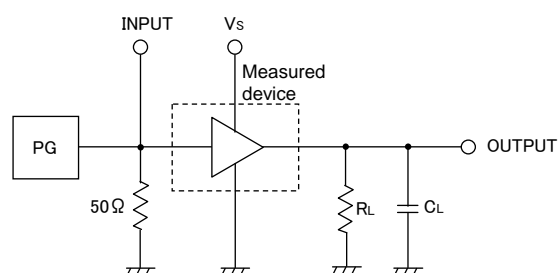
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ*	max	
$I_{S(\text{leak})}$ #	Supply leak current	$V_s = 50\text{V}$ , $V_i = 0.2\text{V}$	—	—	100	$\mu\text{A}$
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_s = 10\text{V}$ , $V_i = 2.4\text{V}$ , $I_o = -350\text{mA}$	—	1.75	2.4	V
		$V_s = 10\text{V}$ , $V_i = 2.4\text{V}$ , $I_o = -100\text{mA}$	—	1.5	2.0	
$I_i$	Input current	$V_i = 5\text{V}$	—	0.48	0.75	mA
		$V_i = 25\text{V}$	—	2.8	4.7	
$I_s$	Supply current	$V_s = 50\text{V}$ , $V_i = 5\text{V}$ (all input)	—	5.6	15.0	mA
$V_F$ #	Clamping diode forward voltage	$I_F = -350\text{mA}$	—	-1.2	-2.4	V
$I_R$	Clamping diode reverse current	$V_R = 50\text{V}$	—	—	100	$\mu\text{A}$

\* : The typical values are those measured under ambient temperature ( $T_a$ ) of  $25^\circ\text{C}$ . There is no guarantee that these values are obtained under any conditions.

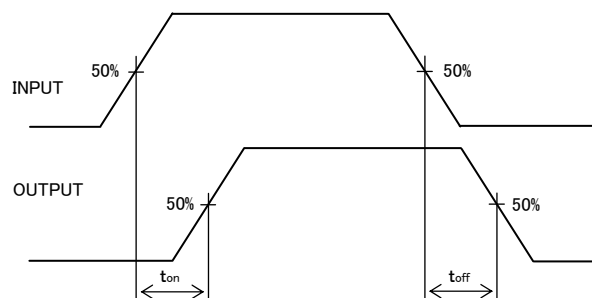
# : Unused Input pins must be connected to GND.

**SWITCHING CHARACTERISTICS** (Unless otherwise noted,  $T_a = 25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
$t_{on}$	Turn-on time	$C_L = 15\text{pF}$ (note 1)	—	110	—	ns
$t_{off}$	Turn-off time		—	5200	—	ns

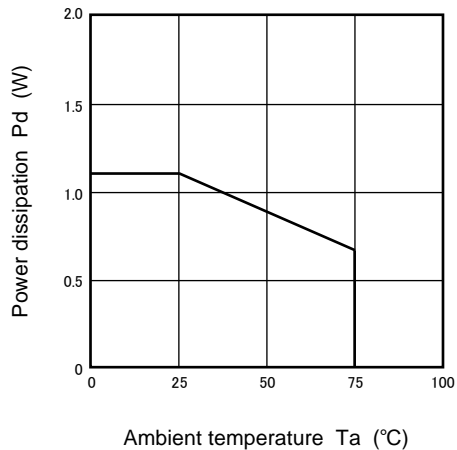
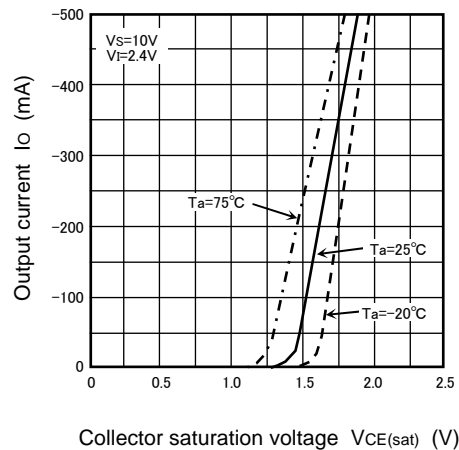
**NOTE 1 TEST CIRCUIT**

- (1) Pulse generator (PG) characteristics:  $\text{PRR} = 1\text{kHz}$ ,  $t_w = 10\text{ms}$ ,  $t_r = 6\text{ns}$ ,  $t_f = 6\text{ns}$ ,  $Z_o = 50\Omega$ ,  $V_i = 0$  to  $2.4\text{V}$
- (2) Input-output conditions :  $R_L = 30\Omega$ ,  $V_s = 10\text{V}$
- (3) Electrostatic capacity  $C_L$  includes floating capacitance at connections and input capacitance at probes

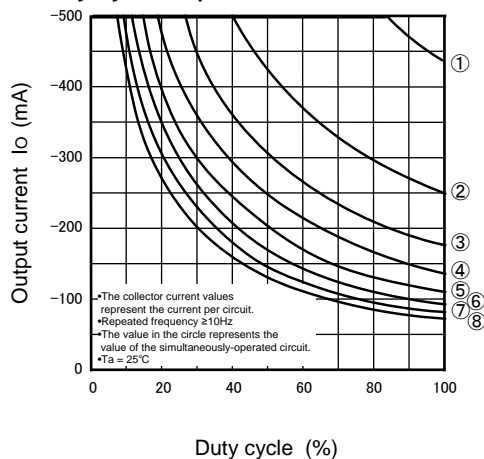
**TIMING DIAGRAM**

## TYPICAL CHARACTERISTICS

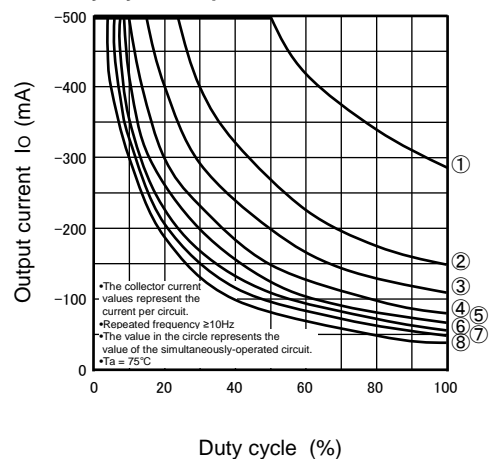
Thermal Derating Factor Characteristics

Output Saturation Voltage  
Collector Current Characteristics

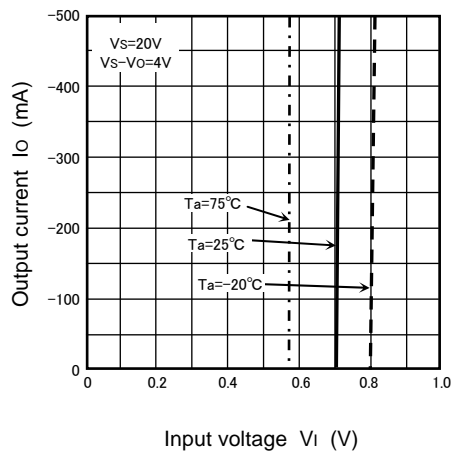
Duty-Cycle-Output current Characteristics



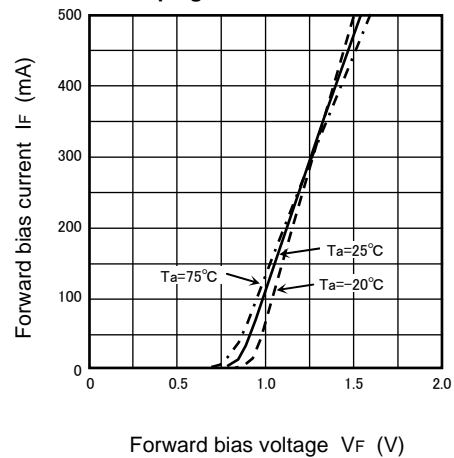
Duty-Cycle-Output current Characteristics

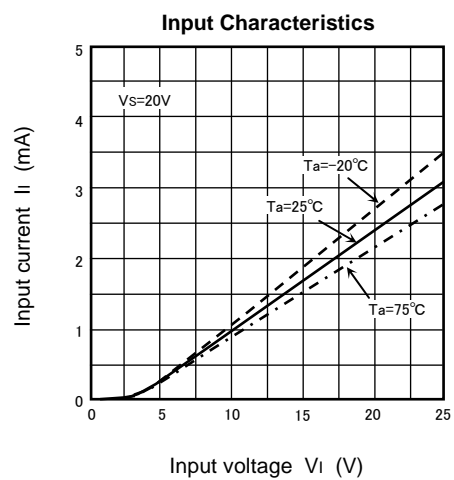
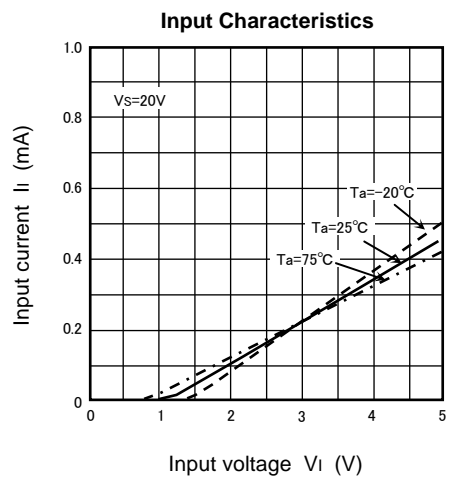


Grounded Emitter Transfer Characteristics



Clamping Diode Characteristics





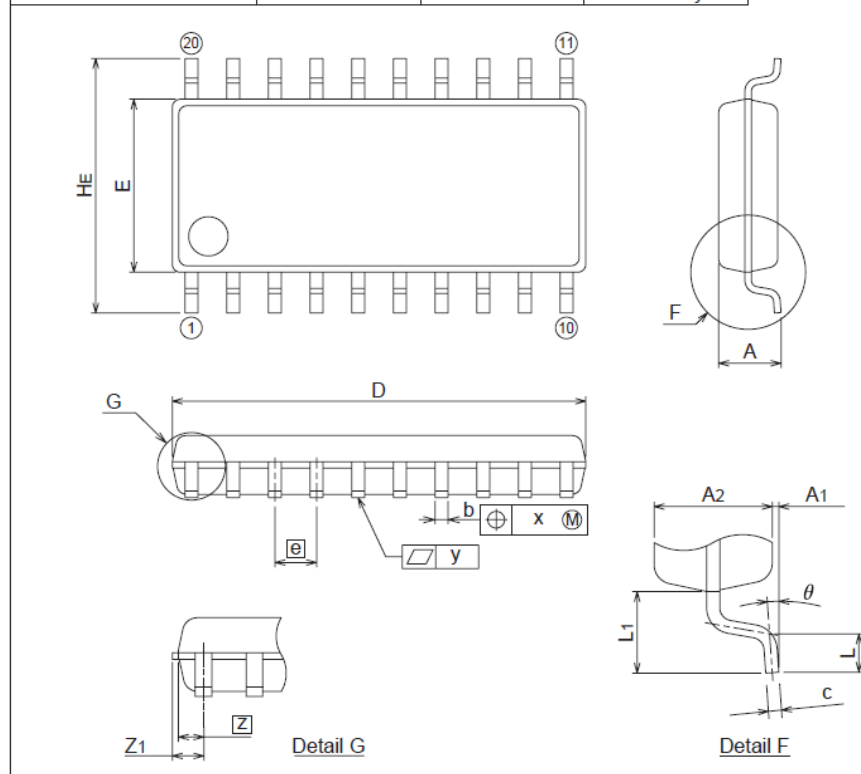
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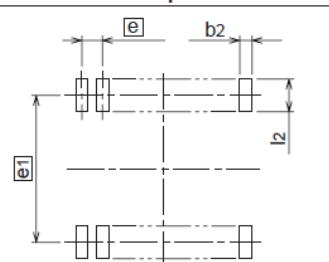
## PACKAGE OUTLINE

**20P2N-A**

JEITA Package Code	JEDEC Code	Weight(g)	Lead Material
P-SOP20-5.3x12.6-1.27	—	0.26	Cu Alloy



## Plastic 20pin 300mil SOP



## Recommended Mount Pad

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	—	—	2.1
A1	0	0.1	0.2
A2	—	1.8	—
b	0.35	0.4	0.5
c	0.18	0.2	0.25
D	12.5	12.6	12.7
E	5.2	5.3	5.4
e	—	1.27	—
HE	7.5	7.8	8.1
L	0.4	0.6	0.8
L1	—	1.25	—
Z	—	0.585	—
Z1	—	—	0.735
x	—	—	0.25
y	—	—	0.1
$\theta$	0°	—	8°
b2	—	0.76	—
e1	—	7.62	—
l2	1.27	—	—

**Keep safety first in your circuit designs!**

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